ABSTRACT OF THE DISCLOSURE

A drive circuit includes a gate voltage detector that detects a gate-emitter voltage Vge that appears between the gate and emitter of a power semiconductor device throughout a detection time period during which a sampler allows the process of detecting the gate-emitter voltage Vge, and that recognizes the occurrence of an abnormality in the power semiconductor device when the gate-emitter voltage Vge exceeds a reference value. Therefore, the drive circuit can protect the power semiconductor device with higher reliability by promptly detecting the occurrence of a short circuit even when the power semiconductor device is resistant to high voltages.